








	<h2>SIR410DP-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SIR410DP-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 20V 35A PPAK SO-8</p> <p>Datenblätter:  SIR410DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 14969 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIR410DP-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 20V 35A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	14969 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	4.2W (Ta), 36W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	35A (Tc)
Rds On (Max) @ Id, Vgs	4.8 mOhm @ 20A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	41nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1600pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)



















































SIR410DP-T1-GE3 ist neu im Original, Suche SIR410DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIR410DP-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SIR410DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIR412DP-T1-E3 Vishay Precision Group SIR412DP-T1-E3 VISHAY</p>	 <p>SIR412DP Vishay Precision Group SIR412DP VISHAY</p>	 <p>SIR410DP-T1 VISHAY SIR410DP-T1 VISHAY</p>	 <p>SIR408DP-T1-GE3 Electro-Films (EF1) / Vishay MOSFET N-CH 25V 50A PPAK SO-8</p>
 <p>SIR410DP SI SIR410DP SI</p>	 <p>SIR410DP-T1-E3 VISHAY SIR410DP-T1-E3 VISHAY</p>	 <p>SIR408DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 25V 50A PPAK SO-8</p>	 <p>SIR412DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 25V 20A PPAK SO-8</p>

heiße Teile

Mehr

 SIR172ADP-T1-GE3	 SIR172ADP-T1-GE3	 SIR172DP	 SIR172DP-T1-E3	 SIR172DP-T1-GE3
 SIR172DP-T1-GE3	 SIR330DP-T1-GE3	 SIR330DP-T1-GE3	 SIR402DP-T1-GE3	 SIR402DP-T1-GE3
 SIR403EDP-T1-GE3	 SIR403EDP-T1-GE3	 SIR404DP	 SIR404DP-T1-E3	 SIR404DP-T1-GE3
 SIR404DP-T1-GE3	 SIR406DP	 SIR406DP-T1-E3	 SIR406DP-T1-GE3	 SIR406DP-T1-GE3
 SIR406DP-T1-GE3-S	 SIR408DP-T1-GE3	 SIR408DP-T1-GE3	 SIR410DP-T1-E3	 SIR410DP-T1-GE3
 SIR412DP	 SIR412DP-T1-E3	 SIR412DP-T1-GE3	 SIR412DP-T1-GE3	 SIR414DP
 SIR414DP-T1-GE3	 SIR414DP-T1-GE3	 SIR416DP	 SIR416DP-T1-E3	 SIR416DP-T1-GE3
 SIR416DP-T1-GE3	 SIR418DP-T1-E3	 SIR418DP-T1-GE3	 SIR418DP-T1-GE3	 SIR422DP-T1-E3
 SIR422DP-T1-GE3	 SIR422DP-T1-GE3	 SIR424DP-T1-GE3	 SIR424DP-T1-GE3	 SIR426DP-T1-GE3
 SIR426DP-T1-GE3	 SIR428DP	 SIR428DP-T1-E3	 SIR428DP-T1-GE3	 SIR432DP-T1-GE3

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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